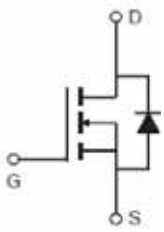
RECTRON SEMICONDUCTOR
TECHNICAL SPECIFICATION

RM150N100AHD

N-Channel Super Trench Power MOSFET

Description

The RM150N100AHD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.



Schematic diagram

TO-263-2L top view

General Features

- V_{DS} =100V,I_D =150A
  $R_{DS(ON)}$ <4.2mΩ @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

100% UIS TESTED!

100% ∆Vds TESTED!

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
150N100	RM150N100AHD	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	20/-12	V
Drain Current-Continuous (Silicon Limited)	I_D	180	A
Drain Current-Continuous (Package Limited)	I_D	150	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	108	A
Pulsed Drain Current	I_{DM}	500	A
Maximum Power Dissipation	P_D	275	W
Derating factor		1.6	W/℃
Single pulse avalanche energy (Note 5)	E_{AS}	378	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	0.7	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

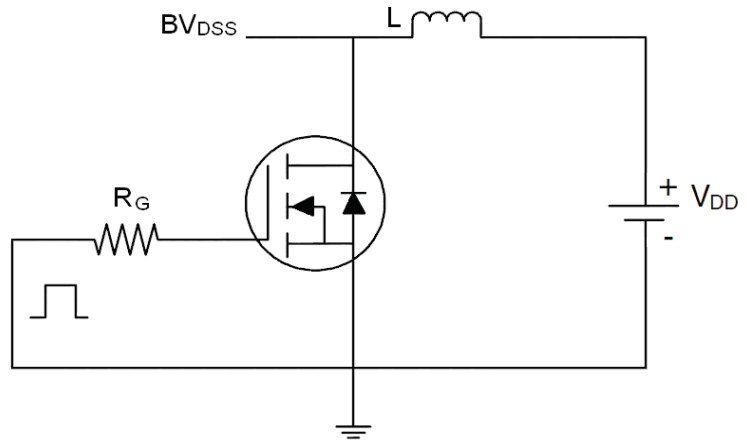
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1	1.5	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D =70A	-	3.5	4.2	mΩ
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=70A	70	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz	-	6680	-	PF
Output Capacitance	C_{oss}		-	1690	-	PF
Reverse Transfer Capacitance	C_{rss}		-	78	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V,I_D=60A V_{GS}=10V,R_G=4.7Ω	-	28	-	nS
Turn-on Rise Time	t_r		-	60	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	16	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=60A, V_{GS}=10V	-	110		nC
Gate-Source Charge	Q_{gs}		-	11.5		nC
Gate-Drain Charge	Q_{gd}		-	28		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=150A	-		1.2	V
Diode Forward Current (Note 2)	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F = I_S di/dt = 100A/μs (Note3)	-	80		nS
Reverse Recovery Charge	Qrr		-	195		nC

Notes:

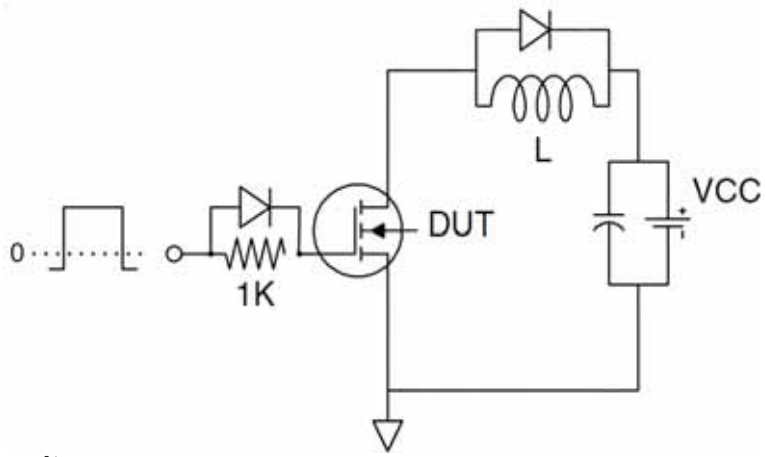
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25Ω

Test Circuit

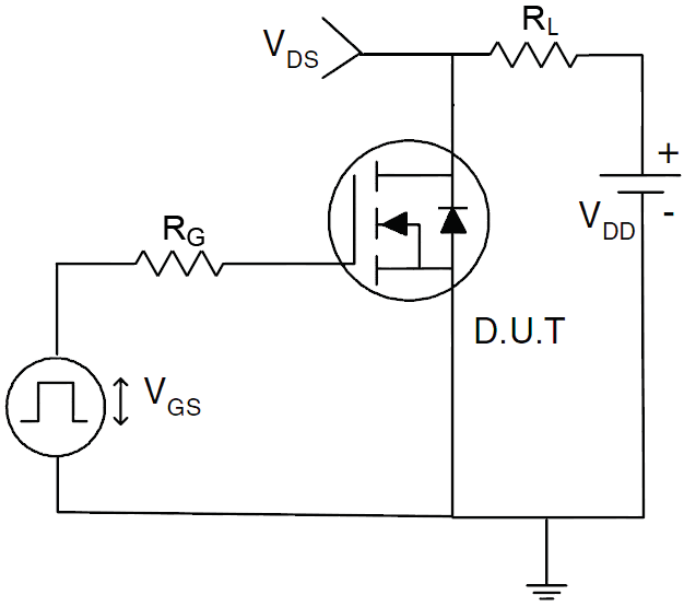
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



RATING AND CHARACTERISTICS CURVES (RM150N100AHD)

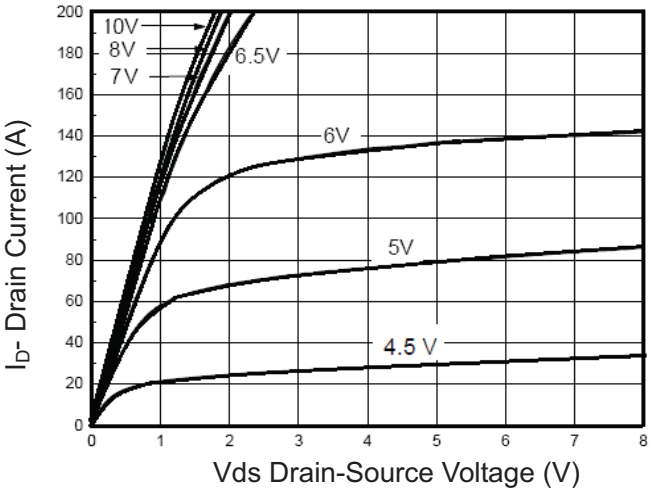


Figure 1 Output Characteristics

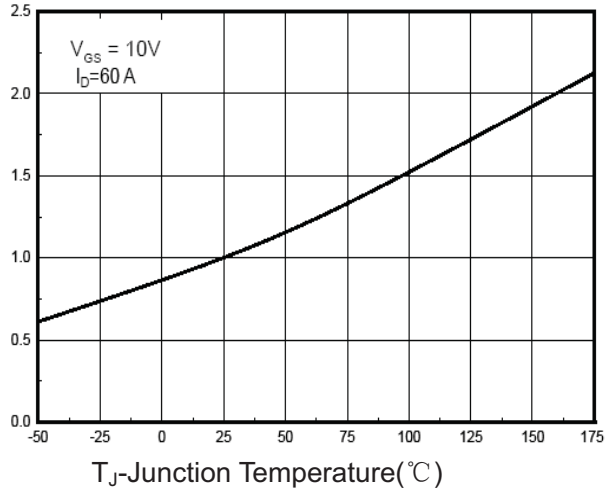


Figure 4 Rdson-JunctionTemperature

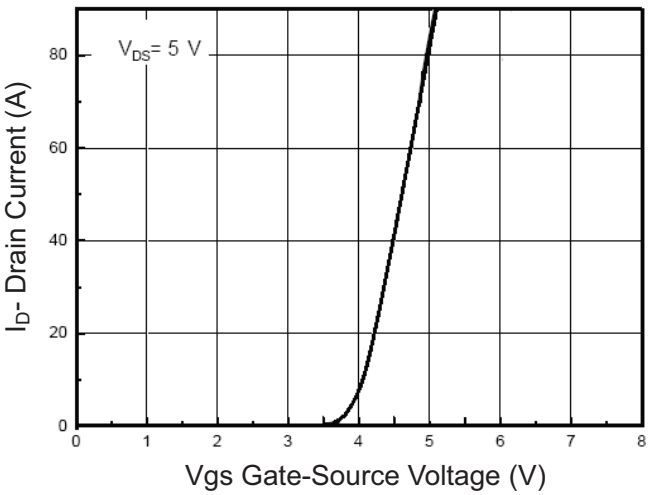


Figure 2 Transfer Characteristics

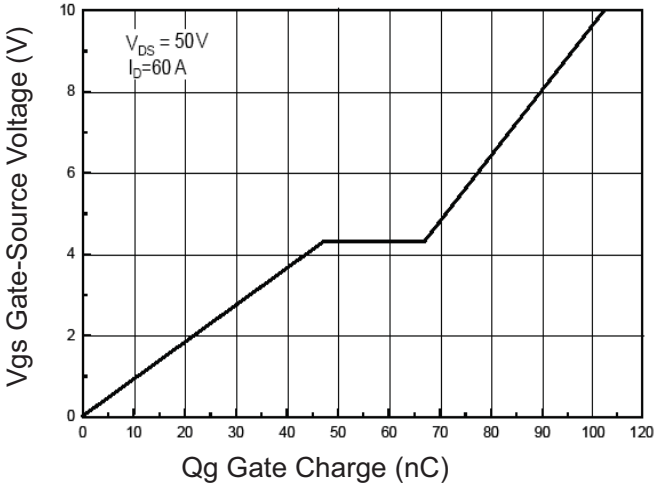


Figure 5 Gate Charge

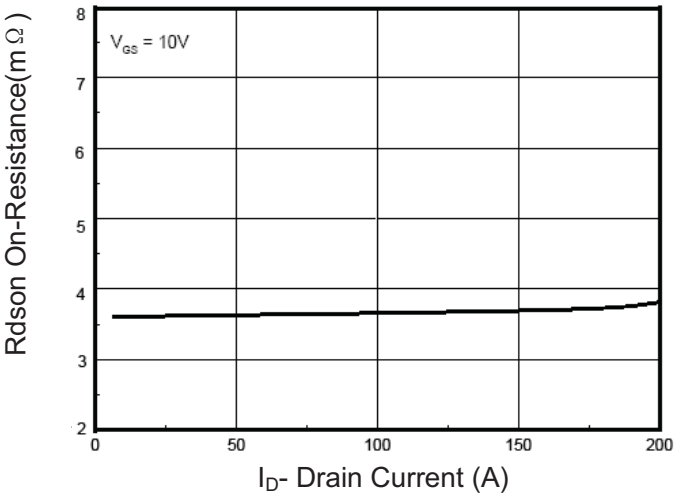


Figure 3 Rdson- Drain Current

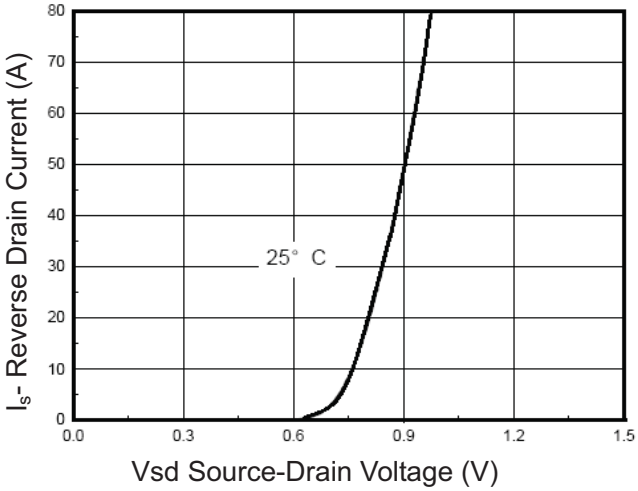


Figure 6 Source- Drain Diode Forward

RATING AND CHARACTERISTICS CURVES (RM150N100AHD)

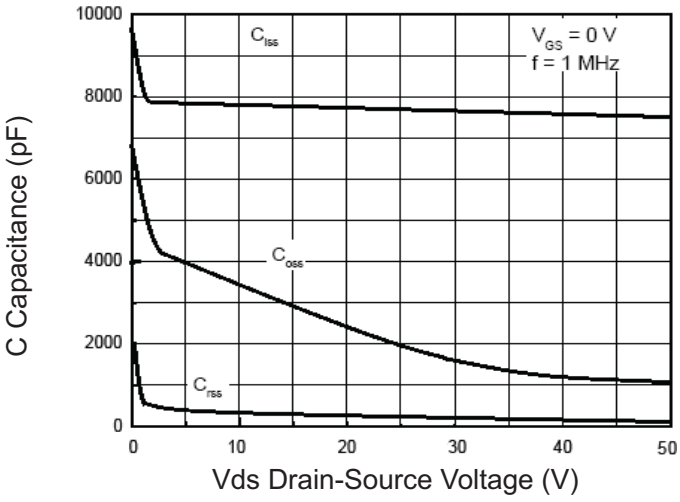


Figure 7 Capacitance vs Vds

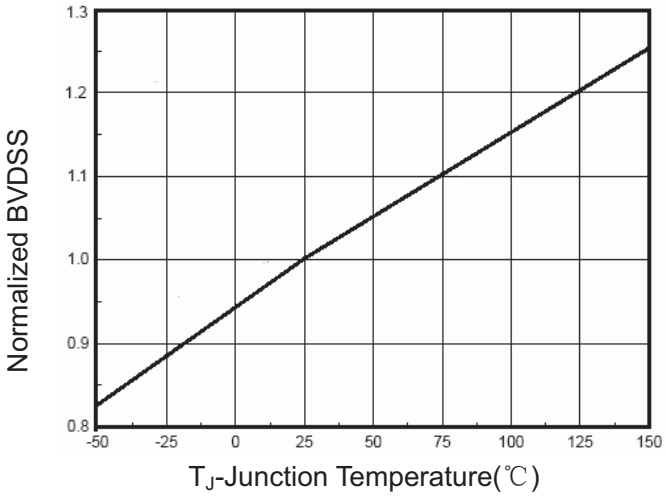


Figure 9 BV_{DSS} vs Junction Temperature

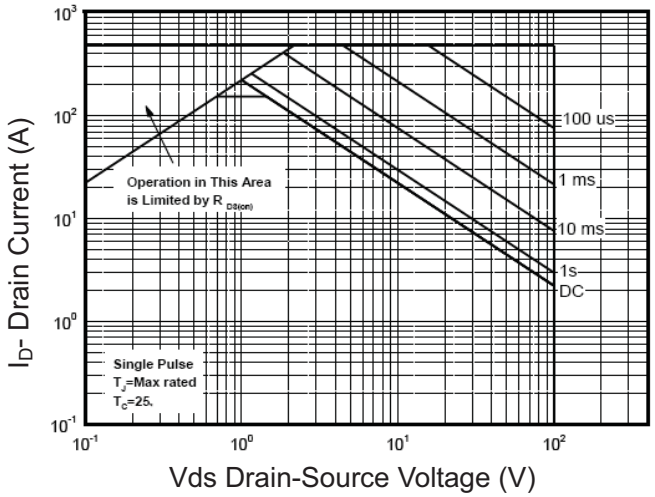


Figure 8 Safe Operation Area

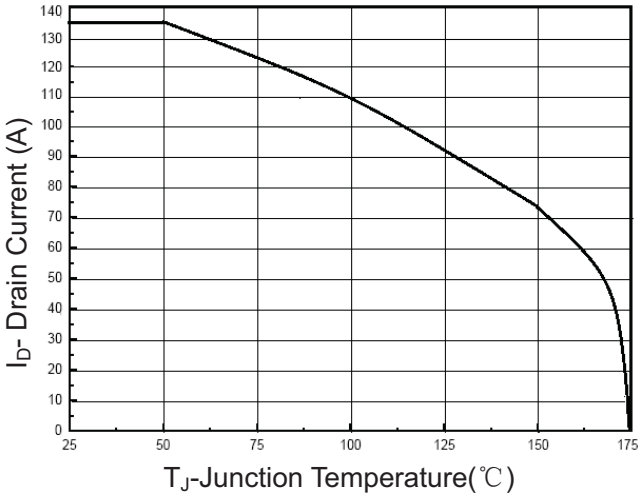


Figure 10 Current De-rating

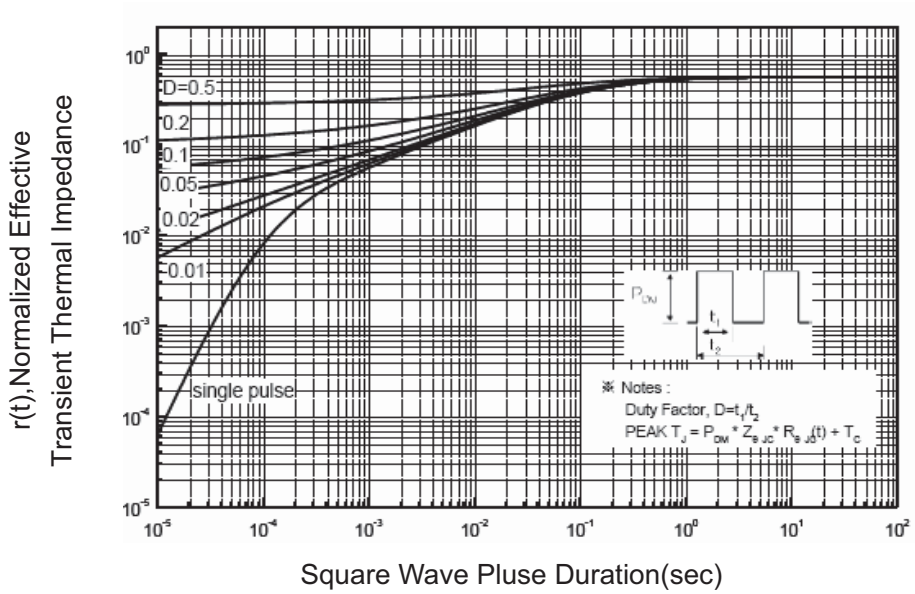
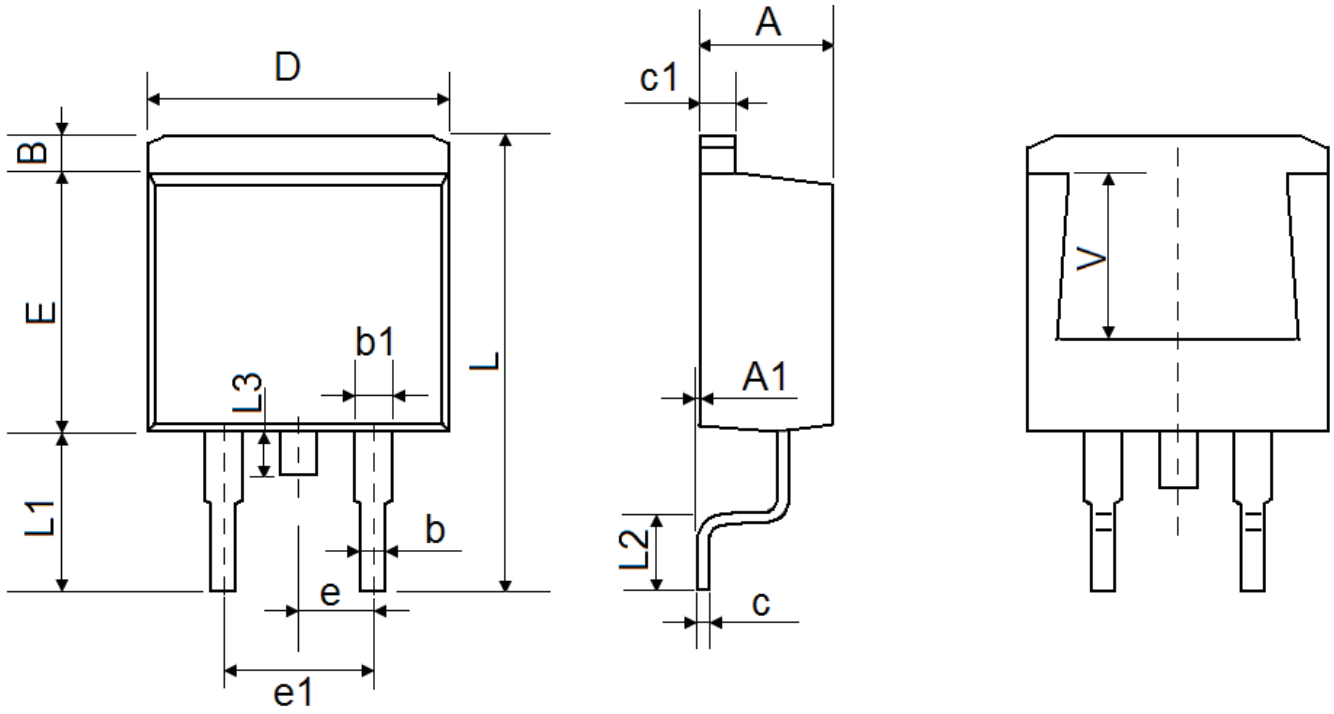


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.470	4.670	0.176	0.184
A1	0.000	0.150	0.000	0.006
B	1.170	1.370	0.046	0.054
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.310	0.530	0.012	0.021
c1	1.170	1.370	0.046	0.054
D	10.010	10.310	0.394	0.406
E	8.500	8.900	0.335	0.350
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
L	15.050	15.450	0.593	0.608
L1	5.080	5.480	0.200	0.216
L2	2.340	2.740	0.092	0.108
L3	1.300	1.700	0.051	0.067
V	5.600 REF		0.220 REF	

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